ABSTRACT OF THE DISCLOSURE

A light emitting layer 4 composed of a single or a plurality of semiconductor layers is laminated on a nondope type, weak p-type, or n-type first semiconductor substrate (not shown in Fig. 1). On the light emitting layer 4, n-type semiconductor layers 5 - 7 composed of a single layer or a plurality of layers are laminated. On the surface of the n-type semiconductor layer 7, a second semiconductor substrate 8 transparent to the wavelength of emitted light from the light emitting layer 4 is formed. Then, the first semiconductor substrate is removed. On the plane exposed by removal of the first semiconductor substrate, a translucent electrode layer 9 transparent to the wavelength of emitted light from the light emitting layer is formed.